Amendments t the Specificati n:

Please replace the paragraph, beginning at page 1, line 9, with the following rewritten paragraph:

The present invention relates to a band elimination filter~~ or the like~~ used in a communication apparatus, such as a cellular phone and car phone.

Please replace the paragraph, beginning at page 1, line 14, with the following rewritten paragraph:

~~Conventionally, ~~In the prior art a surface acoustic wave filter or piezoelectric filter has been used as an RF filter in communication apparatus. The surface acoustic wave filters mainly used include a longitudinal coupled mode filter having a plurality of interdigital transducer electrodes (IDT electrodes) closely arranged in the propagation direction and a ladder filter having surface acoustic wave resonators interconnected in a ladder-like arrangement. On the other hand, as the piezoelectric filter, a bulk wave filter is used. ~~These ~~It has been desired that these filters are ~~expected to be ~~increased in performance and reduced in size.

Please replace the paragraph, beginning at page 3, line 1, with the following rewritten paragraph:

Connecting a plurality of such surface acoustic wave resonators in a ladder arrangement ~~can provide~~provides a ladder surface acoustic wave filter (for example, see Japanese Patent No. 3152418, the ~~entire ~~disclosure of which ~~are~~is incorporated herein by reference in its entirety).

Please replace the paragraph, beginning at page 3, line 6, with the following rewritten paragraph:

~~Now, such ~~Such a conventional acoustic resonator will now be described by taking a surface acoustic wave resonator as an example.

Please replace the paragraph, beginning at page 11, line 18, with the following rewritten paragraph:

FIG. 11(a) shows a maximum attenuation with respect to a normalized impedance.

Please add the following new paragraph after the paragraph ending on line 19 of page 11.

FIG. 11(b) shows an out-of-band loss with respect to the normalized impedance.

Please replace the paragraph, beginning at page 16, line 8, with the following rewritten paragraph:

FIG. 1 shows a configuration of the surface acoustic wave filter and a passing characteristic according to the embodiment 1. ~~In FIG. 1,~~ FIG. 1(a) shows the configuration of the surface acoustic wave filter and FIG. 1(b) shows the passing characteristic. As shown in FIG. 1(a), the surface acoustic wave filter has first and second surface acoustic wave resonators 101 and 102 as acoustic resonators of the present invention and an inductor 103 as a reactance element of the present invention, which couples the resonators with each other. As shown in FIG. 19(a), the surface acoustic wave resonators 101, 102 each have an IDT electrode formed on a piezoelectric substrate, which is equivalent to a piezoelectric substrate according to the present invention, and reflector electrodes disposed on both sides thereof.

Please replace the paragraph, beginning at page 17, line 4, with the following rewritten paragraph:

FIG. 1(b) shows the passing characteristic in the vicinity of a frequency of 900 MHz provided when the inductance of the inductor 103 is set at <u>about</u> 8 nH in the configuration shown in FIG. 1(a). The maximum attenuation is about 38 dB, and a low loss can be attained over wide frequency bands lower and higher a stop band.

Please replace the paragraph, beginning at page 17, line 10, with the following rewritten paragraph:

FIG. 2(a) shows a maximum attenuation with respect to a normalized impedance ($\omega L/Zo$). Here, reference character Zo denotes a characteristic impedance, reference character ω denotes an angular frequency, and reference character L denotes an inductance. The characteristic impedance Zo is set at <u>about</u> 50 Ω. The solid line, the dashed line and the dotted line indicate the maximum attenuation plotted with respect to the impedance for the arrangement according to this embodiment, the maximum attenuation for the arrangement according to the conventional example 1 shown in FIG. 20 and the maximum attenuation for the arrangement according to the conventional example 2 shown in FIG. 21, respectively. FIG. 2(b) shows an out-of-band loss with respect to a normalized impedance. The solid line, the dashed line and the dotted line indicate the out-of-band loss potted with respect to the normalized impedance for the arrangement according to this embodiment, the out-of-band loss for the arrangement according to the conventional example 1 shown in FIG. 20 (b) and the out-of-band loss for the arrangement according to the conventional example 2 shown in FIG. 21 (b),

respectively. In the conventional example 1, while the in-band attenuation is higher than that in the conventional example 2, the out-of-band loss is also higher than that in the conventional example 2. In the conventional example 2, while the out-of-band loss is lower than that in the conventional example 1, the in-band attenuation is also lower than that in the conventional example 1.

Please replace the paragraph, beginning at page 18, line 15, with the following rewritten paragraph:

As for the attenuation characteristic according to this embodiment, the attenuation is higher than that in the conventional example 2 shown in FIG. 21 (b) over the whole range of Z/Zo, and is higher than that in the conventional example 1 shown in FIG. 20 (b) within a range satisfying the relation of Z/Zo>1, and is higher than 40 dB. As for the loss characteristic according to this embodiment, the loss is improved over the whole range of Z/Zo compared to the conventional example 1 shown in FIG. 20 (b), and is improved within a range satisfying the relation of Z/Zo<1.5 compared to the conventional example 2 shown in FIG. 21 (b), and is equal to or less than <u>about</u> 1 dB. That is, within a range of Z between <u>about</u> Zo and 1.5Zo exclusive, both of the attenuation and the loss are improved compared to those in the conventional examples.

Please replace the paragraph, beginning at page 20, line 17, with the following rewritten paragraph:

FIG. 3(a) shows a passing characteristic in the vicinity of a frequency of 900 MHz provided when the inductance value of the inductor is <u>about</u> 8 nH. For comparison, FIG. 3(b) shows a passing characteristic in the vicinity of a frequency of 900 MHz provided in the case where the two surface acoustic wave resonators 1901 and 1902 in the circuit in the conventional example 2 have different resonance frequencies. In this embodiment 2, the stop band is expanded because of the different resonance frequencies. Furthermore, the attenuation is increased and the loss is reduced on both sides of the attenuation band, compared to the passing characteristic in the conventional example 2 shown in FIG. 3(b).

Please replace the paragraph, beginning at page 23, line 15, with the following rewritten paragraph:

FIG. 5(b) shows a passing characteristic according to this embodiment. In FIG. 5(a), the inductor 503 has an inductance of about 10 nH, and the inductors 504, 505 serving as parasitic components have an inductance of about 1 nH.

Please replace the paragraph, beginning at page 26, line 7, with the following rewritten paragraph:

FIGS. 10(a) and 10(b) ~~shows~~show a configuration of the surface acoustic wave filter and a passing characteristic according to the embodiment 4. ~~In FIG. 10,~~ FIG. 10(a) shows the configuration of the surface acoustic wave filter and FIG. 10(b) shows the passing characteristic. As shown in FIG. 10(a), the surface acoustic wave filter has first and second surface acoustic wave resonators 1001 and 1002 and a capacitor 1003 serving as a reactance element that couples the resonators with each other.

Please replace the paragraph, beginning at page 27, line 7, with the following rewritten paragraph:

FIG. 11(a) shows a maximum attenuation with respect to a normalized impedance ($Z = 1/\omega CZo$). Here, reference character Zo denotes a characteristic impedance, reference character ω denotes an angular frequency, and reference character C denotes a capacitance. The characteristic impedance Zo is set at about 50 Ω. The solid line, the dashed line and the dotted line indicate the maximum attenuation with respect to the normalized impedance for the arrangement according to this embodiment, the maximum attenuation for the arrangement according to the conventional example 1 shown in FIG. 20(b) and the maximum attenuation for the arrangement according to the conventional example 2 shown in FIG. 21(b), respectively. As for the attenuation characteristic according to this embodiment, compared to the conventional example 1 shown in FIG. 20(b), the attenuation is increased within a range satisfying the relation of $Z/Zo>1$, and compared to the conventional example 2 shown in FIG. 21(b), the attenuation is increased over the whole range of Z/Zo. FIG. 11(b) shows an out-of-band loss with respect to the normalized impedance. Compared to the conventional example 1 shown in FIG. 20(b), the loss is improved within a range satisfying the relation of $Z/Zo<1.5$.

Please delete line 13 on page 42:

~~Advantages of the Invention~~